NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE3025G uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

V_{DS} =30V,I_D =25A

 $R_{DS(ON)}$ < 10m Ω @ V_{GS} =10V

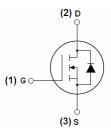
 $R_{DS(ON)}$ < 14m Ω @ V_{GS} =4.5V

- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- SMPS and general purpose applications
- Hard switched and high frequency circuits
- Uninterruptible power supply

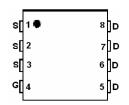
100% UIS TESTED!



Schematic diagram



Marking and pin assignment



DFN 5x6 EP top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE3025G	NCE3025G	DFN 5x6 EP	-	-	-

Absolute Maximum Ratings (T_C=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	30	V	
Gate-Source Voltage	V _{GS}	±20	V	
Drain Current-Continuous	I _D	25	Α	
Drain Current-Continuous(T _C =100 °C)	I _D (100℃)	17	Α	
Pulsed Drain Current ^(Note 1)	I _{DM}	50	Α	
Maximum Power Dissipation	P _D	30	W	
Derating factor		0.24	W/℃	
Single pulse avalanche energy (Note 5)	E _{AS}	70	mJ	
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 150	$^{\circ}\!\mathbb{C}$	

Thermal Characteristic

Electrical Characteristics (T_C=25°C unless otherwise noted)

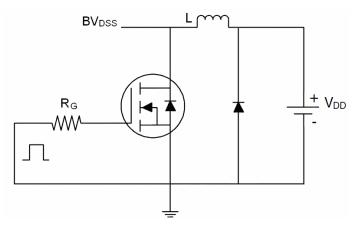
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	30	33	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =30V, V_{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V_{GS} =±20V, V_{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)			•			
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	1	1.6	3	V
Davis Course On Otata Basistana	R _{DS(ON)}	V _{GS} =10V, I _D =10A	-	7.0	10	mΩ
Drain-Source On-State Resistance		V _{GS} =4.5V, I _D =10A	-	10.5	14	
Forward Transconductance	g FS	V _{DS} =5V,I _D =20A	15	-	-	S
Dynamic Characteristics (Note4)			•			
Input Capacitance	C _{lss})/ 45)/)/ O)/	-	1593.9	-	PF
Output Capacitance	Coss	V_{DS} =15V, V_{GS} =0V,	-	192.3	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	-	176.8	-	PF
Switching Characteristics (Note 4)			•			
Turn-on Delay Time	t _{d(on)}		-	10	-	nS
Turn-on Rise Time	t _r	V_{DD} =15 V , I_{D} =10 A	-	8	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{GEN} =1.8 Ω	-	30	-	nS
Turn-Off Fall Time	t _f		-	5	-	nS
Total Gate Charge	Qg	\/ -45\/1 -404	-	32.6	-	nC
Gate-Source Charge	Q_{gs}	V_{DS} =15V, I_{D} =10A, V_{GS} =10V	-	5.5	-	nC
Gate-Drain Charge	Q_{gd}	V _{GS} -10V	-	6	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V _{GS} =0V,I _S =10A	-	0.85	1.2	V
Diode Forward Current (Note 2)	Is		-	-	25	Α
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF = 10A	-	22	35	nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	-	12	20	nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

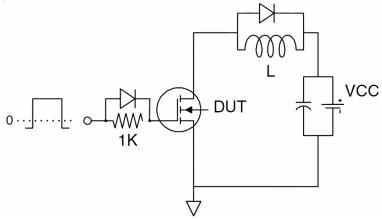
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- **4.** Guaranteed by design, not subject to production
- **5.** EAS condition: Tj=25 $^{\circ}$ C,V_{DD}=15V,V_G=10V,L=0.5mH,Rg=25 Ω

Test Circuit

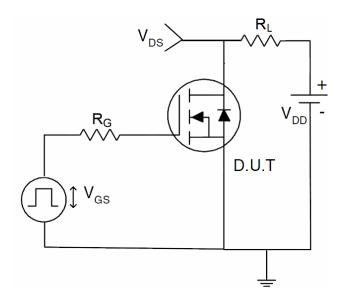
1) E_{AS} Test Circuits



2) Gate Charge Test Circuit:



3) Switch Time Test Circuit:



Typical Electrical and Thermal Characteristics (Curves)

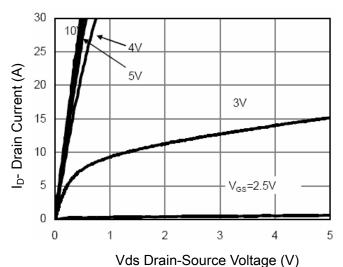


Figure 1 Output Characteristics

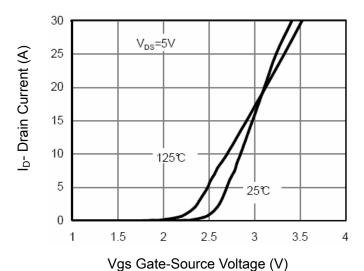


Figure 2 Transfer Characteristics

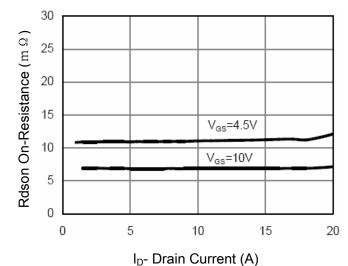


Figure 3 Rdson- Drain Current

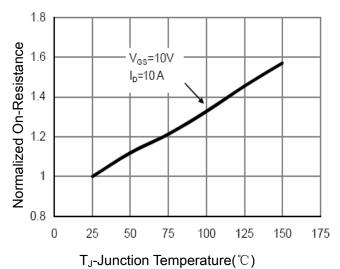


Figure 4 Rdson-Junction Temperature

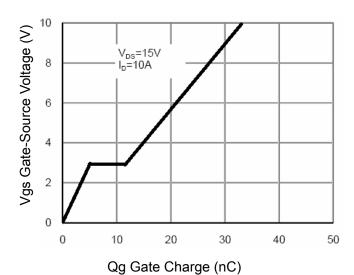


Figure 5 Gate Charge

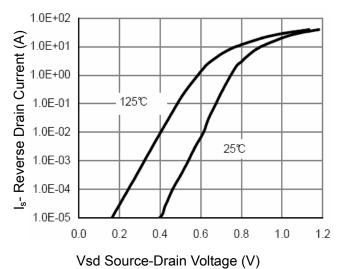


Figure 6 Source- Drain Diode Forward



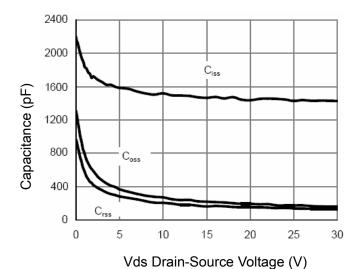


Figure 7 Capacitance vs Vds

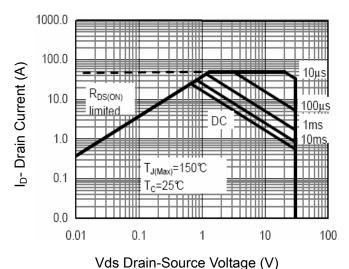


Figure 8 Safe Operation Area

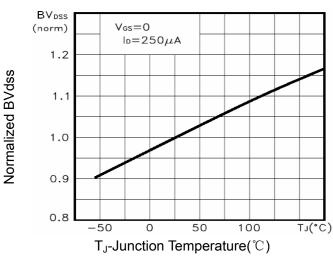
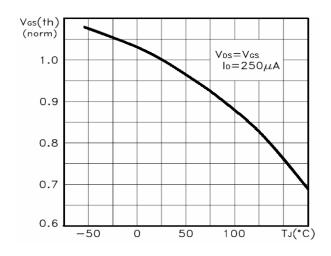


Figure 9 BV_{DSS} vs Junction Temperature



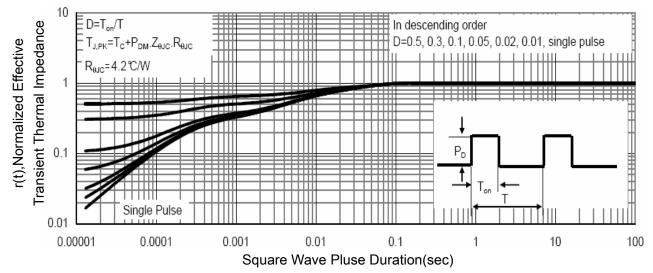
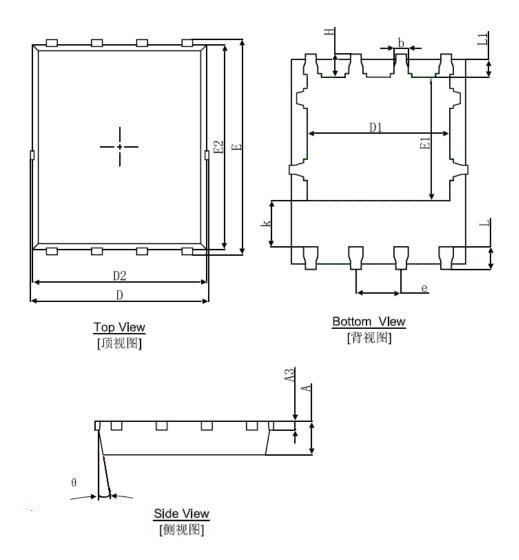


Figure 11 Normalized Maximum Transient Thermal Impedance

DFN5X6-8L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min.	Max.	Min.	Max.	
Α	0.900	1.000	0.035	0.039	
A3	0.254REF.		0.010REF.		
D	4.944	5.096	0.195	0.201	
E	5.974	6.126	0.235	0.241	
D1	3.910	4.110	0.154	0.162	
E1	3.375	3.575	0.133	0.141	
D2	4.824	4.976	0.190	0.196	
E2	5.674	5.826	0.223	0.229	
k	1.190	1.390	0.047	0.055	
b	0.350	0.450	0.014	0.018	
е	1.270TYP.		0.050TYP.		
L	0.559	0.711	0.022	0.028	
L1	0.424	0.576	0.017	0.023	
Н	0.574	0.726	0.023	0.029	
θ	8°	12°	8°	12°	

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